

Complementary power Darlington transistors

Features

- Good h_{FE} linearity
- High f_T frequency
- Monolithic Darlington configuration with integrated antiparallel collector-emitter diode

Applications

■ Linear and switching industrial equipment

Description

The devices are manufactured in planar technology with "base island" layout and monolithic Darlington configuration.

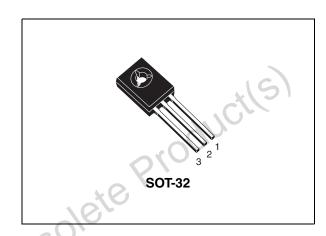


Figure 1. Internal schematic diagram

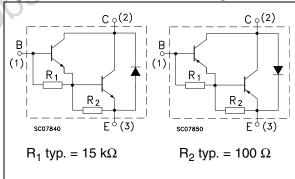


Table 1. Device summary

Order codes	Marking	Polarity	Package	Packaging
2N6036	2N6036	NPN	SOT-32	Tube
2N6039	2N6039	PNP	SOT-32	Tube

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1 Absolute maximum ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	80	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	80	V
V _{EBO}	Emitter-base voltage (I _C = 0)	5	V
I _C	Collector current	4	Α
I _{CM}	Collector peak current	8	А
I _B	Base current	0.1	Α
P _{TOT}	Total dissipation at T _{case} = 25°C	40	W
T _{STG}	Storage temperature	-65 to 150	°C
T _J	Max. operating junction temperature	150	°C

Note: For PNP types voltage and current values are negative.



2 Electrical characteristics

(T_{case} = 25 °C; unless otherwise specified)

Table 3. Electrical characteristics

Symbol	Parameter	Test cond	itions	Min.	Тур.	Max.	Unit
I _{CEV}	Collector cut-off current (V _{BE} = -1.5 V)	V _{CE} = 80 V V _{CE} = 80 V, T _c =	= 125 °C		-	0.1 0.5	mA mA
I _{CBO}	Collector cut-off current (I _E = 0)	V _{CB} = 80 V			-	0.1	mA
I _{CEO}	Collector cut-off current $(I_B = 0)$	V _{CE} = 80 V				0.1	mA
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = 5 V		(0)). 	2	mA
V _{CEO(sus)} ⁽¹⁾	Collector-emitter sustaining voltage	I _C = 100 mA	10	80	-		٧
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	I _C = 2 A	$I_B = 8 \text{ mA}$		-	2	V
		$I_C = 4 A$	I _B = 40 mA		-	3	٧
V _{BE(sat)} ⁽¹⁾	Base-emitter saturation voltage	I _C = 4 A	I _B = 40 mA		1	4	٧
V _{BE(on)}	Base-emitter on voltage	I _C = 2 A	V _{CE} = 3 V		-	2.8	٧
		$I_C = 0.5 A$	V _{CE} = 3 V	500	-		
h _{FE} ⁽¹⁾	DC current gain	I _C = 2 A	V _{CE} = 3 V	750	-	15000	
	00,	I _C = 4 A	V _{CE} = 3 V	100	-		
h _{fe}	Small signal current gain	I _C = 0.75 A V f = 1 MHz	/ _{CE} = 10 V	25	-		
C _{CBO}	Collector base capacitance (I _E = 0)	V _{CB} = 10 V f for 2N6036 for 2N6039	= 0.1 MHz		-	100 200	pF pF

^{1.} Pulsed duration = 300 μs, duty cycle 1.5%.

Note: For PNP types voltage and current values are negative.

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2.1 **Typical characteristic (curves)**

Figure 2. DC current gain

 $(V_{CE} = 3 V NPN)$ 6000 4000 2000 1000 600 400 V_{CE}=3V 200 100 L 0.1 $I_{C}(A)$

Figure 3. DC current gain $(V_{CE} = -3 V PNP)$

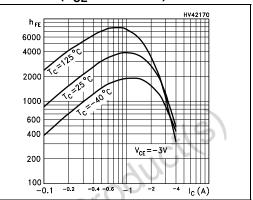


Figure 4. DC current gain $(V_{CE} = 5 V NPN)$

Figure 5. DC current gain $(V_{CE} = -5 V PNP)$ HV42160 h FE h FE 6000 6000

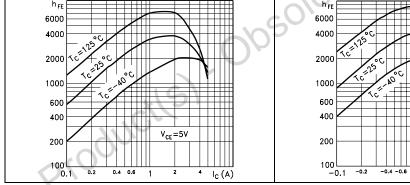


Figure 6. **Collector-emitter saturation** voltage (NPN)

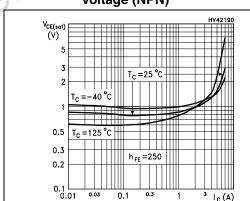
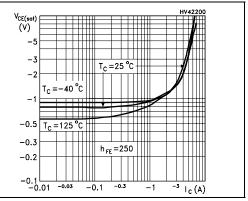


Figure 7. **Collector-emitter saturation** voltage (PNP)



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Figure 8. Base-emitter saturation voltage (NPN)

VBE(sat) (V) 2 1.75 1.5 1.25 1 0.75 0.1 0.2 0.4 0.6 1 2 4 Ic (A)

Figure 9. Base-emitter saturation voltage (PNP)

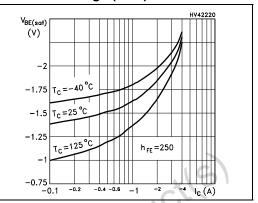
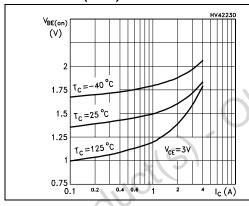


Figure 10. Base-emitter on voltage (NPN)

Figure 11. Base-emitter on voltage (PNP)



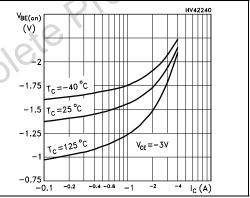
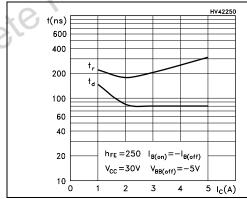
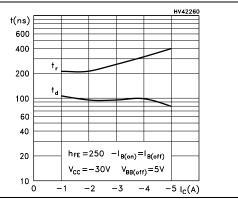


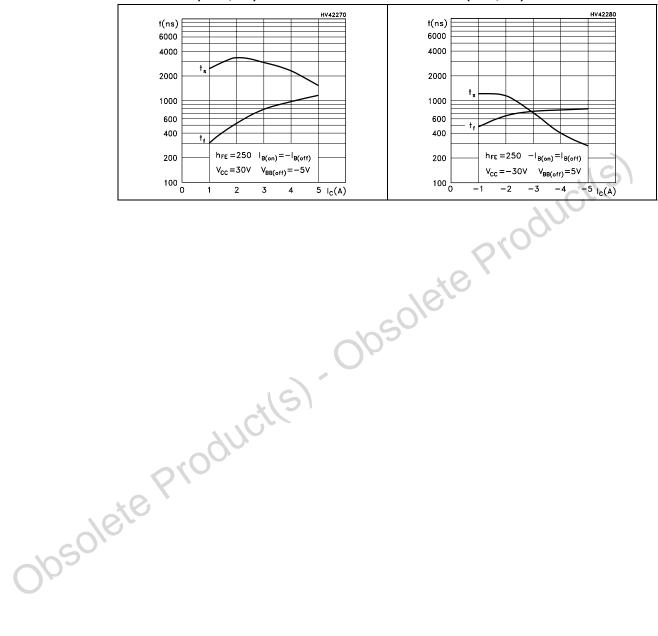
Figure 12. Resistive load switching time Figure 13. Resistive load switching time (NPN, on) (PNP, on)





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Figure 14. Resistive load switching time Figure 15. Resistive load switching time (NPN, off) (PNP, off)



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3 Package mechanical data

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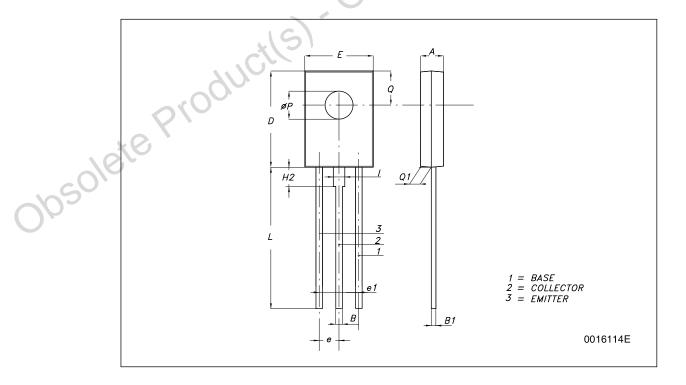
Obsolete Product(s). Obsolete Product(s)



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DIM.	mm.				
DIWI.	MIN.	ТҮР	MAX.		
А	2.4		2.9		
В	0.64		0.88		
B1	0.39		0.63		
D	10.5		11.05		
E	7.4		7.8		
е	2.04	2.29	2.54		
e1	4.07	4.58	5.08		
L	15.3		16		
Р	2.9		3.2		
Q		3.8			
Q1	1	3/8	1.52		
H2		2.15			
I		1.27			



2N6036, 2N6039 Revision history

4 Revision history

Table 4. Document revision history

	Date	Revision	Changes
	21-Jun-2004	4	Document migration, no content change.
	20-May-2009	5	Modified SOT-32 mechanical data.
obsole	ie Prod	ucil	Modified SOT-32 mechanical data.

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